# Octal D-Type Flip-Flop with 3-State Outputs

# With 5V-Tolerant Inputs

The MC74LVX374 is an advanced high speed CMOS octal D-type flip-flop with 3-state outputs. The inputs tolerate voltages up to 7.0 V, allowing the interface of 5.0 V systems to 3.0 V systems.

This 8-bit D-type flip-flop is controlled by a clock input and an output enable input. When the output enable input is high, the eight outputs are in a high impedance state.

#### **Features**

- High Speed:  $f_{max} = 160 \text{ MHz}$  (Typ) at  $V_{CC} = 3.3 \text{ V}$
- Low Power Dissipation:  $I_{CC} = 4 \mu A \text{ (Max)}$  at  $T_A = 25 \text{°C}$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Low Noise:  $V_{OLP} = 0.8 \text{ V (Max)}$
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300 mA
- ESD Performance:

Human Body Model > 2000 V; Machine Model > 200 V

• These Devices are Pb-Free and are RoHS Compliant



## ON Semiconductor®

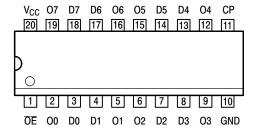
## http://onsemi.com





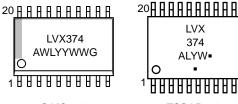
SOIC-20 DW SUFFIX CASE 751D TSSOP-20 DT SUFFIX CASE 948E

#### **PIN ASSIGNMENT**



20-Lead (Top View)

## **MARKING DIAGRAMS**



SOIC-20

TSSOP-20

LVX374 = Specific Device Code A = Assembly Location

WL, L = Wafer Lot Y = Year WW, W = Work Week G or = Pb-Free Package

(Note: Microdot may be in either location)

#### **PIN NAMES**

Pins	Function
OE	Output Enable Input
CP	Clock Pulse Input
D0-D7	Data Inputs
O0-O7	3-State Outputs

#### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

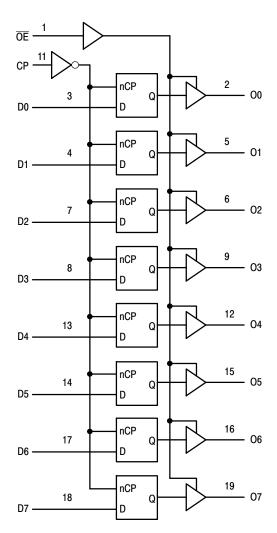


Figure 1. Logic Diagram

	INPUTS		OUTPUTS	
ŌĒ	СР	Dn	On	OPERATING MODE
L L	<b>↑</b>	l h	L H	Load and Read Register
L	1	Х	NC	Hold and Read Register
Н	1	Х	Z	Hold and Disable Outputs
H H	<b>↑</b>	l h	Z Z	Load Internal Register and Disable Outputs

 $H = High\ Voltage\ Level;\ h = High\ Voltage\ Level\ One\ Setup\ Time\ Prior\ to\ the\ Low-to-High\ Clock\ Transition;\ L = Low\ Voltage\ Level;\ l = Low\ Voltage\ Level\ One\ Setup\ Time\ Prior\ to\ the\ Low-to-High\ Clock\ Transition;\ NC = No\ Change,\ State\ Prior\ to\ Low-to-High\ Clock\ Transition;\ X = High\ or\ Low\ Voltage\ Level\ and\ Transitions\ are\ Acceptable;\ Z = High\ Impedance\ State;\ \uparrow = Low-to-High\ Transition;\ \uparrow = Not\ a\ Low-to-High\ Transition;\ For\ I_{CC}\ Reasons\ DO\ NOT\ FLOAT\ Inputs$ 

#### **MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	DC Supply Voltage	-0.5 to +7.0	V
V <sub>in</sub>	DC Input Voltage	-0.5 to +7.0	V
V <sub>out</sub>	DC Output Voltage	-0.5 to V <sub>CC</sub> +0.5	V
I <sub>IK</sub>	Input Diode Current	-20	mA
lok	Output Diode Current	±20	mA
l <sub>out</sub>	DC Output Current, per Pin	±25	mA
Icc	DC Supply Current, V <sub>CC</sub> and GND Pins	±75	mA
P <sub>D</sub>	Power Dissipation	180	mW
T <sub>stg</sub>	Storage Temperature	-65 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

## RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V <sub>CC</sub>	DC Supply Voltage	2.0	3.6	V
V <sub>in</sub>	DC Input Voltage	0	5.5	V
V <sub>out</sub>	DC Output Voltage		V <sub>CC</sub>	V
T <sub>A</sub>	Operating Temperature, All Package Types		+85	°C
Δt/ΔV	Input Rise and Fall Time	0	100	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

## DC ELECTRICAL CHARACTERISTICS

			v <sub>cc</sub>	Т	<sub>A</sub> = 25°	С	$T_A = -40$	to 85°C	
Symbol	Parameter	Test Conditions	V	Min	Тур	Max	Min	Max	Unit
V <sub>IH</sub>	High-Level Input Voltage		2.0 3.0 3.6	1.5 2.0 2.4			1.5 2.0 2.4		V
V <sub>IL</sub>	Low-Level Input Voltage		2.0 3.0 3.6			0.5 0.8 0.8		0.5 0.8 0.8	V
V <sub>OH</sub>	High-Level Output Voltage (V <sub>in</sub> = V <sub>IH</sub> or V <sub>IL</sub> )	$I_{OH} = -50 \mu A$ $I_{OH} = -50 \mu A$ $I_{OH} = -4 \text{ mA}$	2.0 3.0 3.0	1.9 2.9 2.58	2.0 3.0		1.9 2.9 2.48		V
V <sub>OL</sub>	Low-Level Output Voltage (V <sub>in</sub> = V <sub>IH</sub> or V <sub>IL</sub> )	$I_{OL} = 50 \ \mu\text{A}$ $I_{OL} = 50 \ \mu\text{A}$ $I_{OL} = 4 \ \text{mA}$	2.0 3.0 3.0		0.0 0.0	0.1 0.1 0.36		0.1 0.1 0.44	V
l <sub>in</sub>	Input Leakage Current	V <sub>in</sub> = 5.5 V or GND	3.6			±0.1		±1.0	μΑ
l <sub>OZ</sub>	Maximum 3–State Leakage Current	$V_{in} = V_{IL} \text{ or } V_{IH}$ $V_{out} = V_{CC} \text{ or GND}$	3.6			±0.2 5		±2.5	μΑ
Icc	Quiescent Supply Current	V <sub>in</sub> = V <sub>CC</sub> or GND	3.6			4.0		40.0	μΑ

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

## AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3.0 \text{ns}$ )

				Т	<sub>A</sub> = 25°	С	$T_A = -40$	to 85°C	
Symbol	Parameter	Test Cond	ditions	Min	Тур	Max	Min	Max	Unit
f <sub>max</sub>	Maximum Clock Frequency (50% Duty Cycle)	V <sub>CC</sub> = 2.7 V	$C_L = 15 \text{ pF}$ $C_L = 50 \text{ pF}$	60 45	115 60		50 40		MHz
		$V_{CC} = 3.3 \pm 0.3 \text{ V}$	$C_L = 15 \text{ pF}$ $C_L = 50 \text{ pF}$	100 60	160 95		85 55		
t <sub>PLH</sub> , t <sub>PHL</sub>	Propagation Delay CP to O	V <sub>CC</sub> = 2.7 V	$C_L = 15 \text{ pF}$ $C_L = 50 \text{ pF}$		8.5 11.0	16.3 19.8	1.0 1.0	19.5 23.0	ns
		$V_{CC} = 3.3 \pm 0.3 \text{ V}$	$C_L = 15 \text{ pF}$ $C_L = 50 \text{ pF}$		6.7 9.2	10.6 14.1	1.0 1.0	12.5 16.0	
t <sub>PZL</sub> , t <sub>PZH</sub>	Output Enable Time OE to O	$V_{CC} = 2.7 \text{ V}$ $R_L = 1 \text{ k}\Omega$	C <sub>L</sub> = 15 pF C <sub>L</sub> = 50 pF		7.6 10.1	14.5 18.0	1.0 1.0	17.5 21.0	ns
		$V_{CC} = 3.3 \pm 0.3 \text{ V}$ $R_L = 1 \text{ k}\Omega$	$C_L = 15 \text{ pF}$ $C_L = 50 \text{ pF}$		5.9 8.4	9.3 12.8	1.0 1.0	11.0 14.5	
t <sub>PLZ</sub> , t <sub>PHZ</sub>	Output Disable Time OE to O	$V_{CC} = 2.7 \text{ V}$ $R_L = 1 \text{ k}\Omega$	C <sub>L</sub> = 50 pF		11.5	18.5	1.0	22.0	ns
		$V_{CC} = 3.3 \pm 0.3 \text{ V}$ $R_L = 1 \text{ k}\Omega$	C <sub>L</sub> = 50 pF		9.6	13.2	1.0	15.0	
t <sub>OSHL</sub> t <sub>OSLH</sub>	Output-to-Output Skew (Note 1)	$V_{CC} = 2.7 \text{ V}$ $V_{CC} = 3.3 \pm 0.3 \text{ V}$				1.5 1.5		1.5 1.5	ns

Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device.
 The specification applies to any outputs switching in the same direction, either HIGH-to-LOW (t<sub>OSHL</sub>) or LOW-to-HIGH (t<sub>OSLH</sub>); parameter guaranteed by design.

#### **CAPACITIVE CHARACTERISTICS**

		T <sub>A</sub> = 25°C		T <sub>A</sub> = -40 to 85°C			
Symbol	Parameter	Min	Тур	Max	Min	Max	Unit
Cin	Input Capacitance		4	10		10	pF
C <sub>out</sub>	Maximum Three–State Output Capacitance		6				pF
C <sub>PD</sub>	Power Dissipation Capacitance (Note 2)		32				pF

<sup>2.</sup> C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I<sub>CC(OPR)</sub> = C<sub>PD</sub> • V<sub>CC</sub> • f<sub>in</sub> + I<sub>CC</sub>/8 (per flip–flop). C<sub>PD</sub> is used to determine the no–load dynamic power consumption; P<sub>D</sub> = C<sub>PD</sub> • V<sub>CC</sub><sup>2</sup> • f<sub>in</sub> + I<sub>CC</sub> • V<sub>CC</sub>.

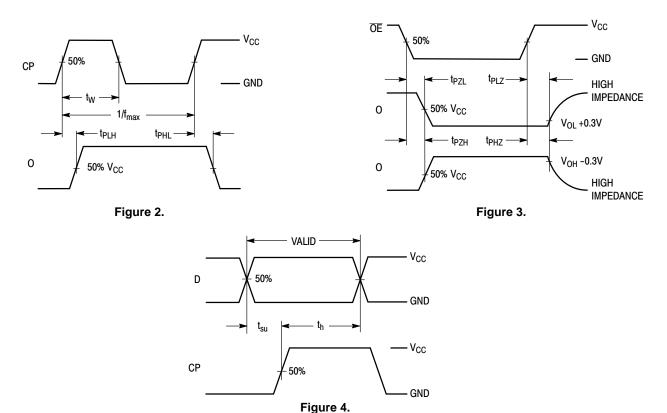
## **NOISE CHARACTERISTICS** (Input $t_r = t_f = 3.0 \text{ns}$ , $C_L = 50 \text{pF}$ , $V_{CC} = 3.3 \text{V}$ , Measured in SOIC Package)

		T <sub>A</sub> = 25°C		
Symbol	Characteristic	Тур	Max	Unit
V <sub>OLP</sub>	Quiet Output Maximum Dynamic V <sub>OL</sub>	0.5	0.8	V
V <sub>OLV</sub>	Quiet Output Minimum Dynamic V <sub>OL</sub>	-0.5	-0.8	V
V <sub>IHD</sub>	Minimum High Level Dynamic Input Voltage		2.0	V
V <sub>ILD</sub>	Maximum Low Level Dynamic Input Voltage		0.8	V

## **TIMING REQUIREMENTS** (Input $t_r = t_f = 3.0 \text{ns}$ )

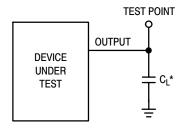
			T <sub>A</sub> = 25°C		T <sub>A</sub> = -40 to 85°C	
Symbol	Parameter	Test Conditions	Тур	Limit	Limit	Unit
t <sub>w</sub>	Minimum Pulse Width, CP	$V_{CC} = 2.7 \text{ V}$ $V_{CC} = 3.3 \pm 0.3 \text{ V}$		7.5 5.0	8.0 5.5	ns
t <sub>su</sub>	Minimum Setup Time, D to CP	$V_{CC} = 2.7 \text{ V}$ $V_{CC} = 3.3 \pm 0.3 \text{ V}$		6.5 4.5	6.5 4.5	ns
t <sub>h</sub>	Minimum Hold Time, D to CP	$V_{CC} = 2.7 \text{ V}$ $V_{CC} = 3.3 \pm 0.3 \text{ V}$		2.0 2.0	2.0 2.0	ns

## **SWITCHING WAVEFORMS**



## **TEST CIRCUITS**

DEVICE



\*Includes all probe and jig capacitance

Figure 5. Propagation Delay Test Circuit

UNDER TESTING tPHZ AND tPZH. C<sub>L</sub>\* **TEST** 

OUTPUT

\*Includes all probe and jig capacitance

 $1 \, \mathrm{k}\Omega$ 

CONNECT TO  $V_{CC}$  WHEN TESTING  $t_{PLZ}$  AND  $t_{PZL}.$ 

CONNECT TO GND WHEN

**TEST POINT** 

Figure 6. Three-State Test Circuit

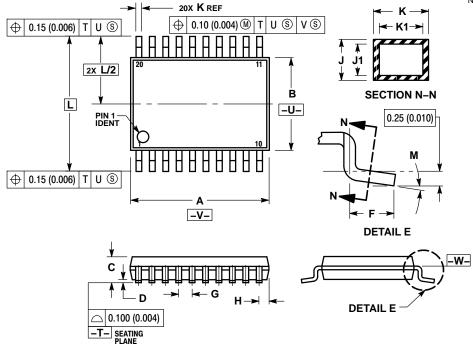
## **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MC74LVX374DWR2G	SOIC-20 (Pb-Free)	1000 Tape & Reel
MC74LVX374DTR2G	TSSOP-20 (Pb-Free)	2500 Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

## PACKAGE DIMENSIONS

## TSSOP-20 CASE 948E-02 **ISSUE C**



#### NOTES:

- OTES:

  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

  2. CONTROLLING DIMENSION:
  MILLIMETER.

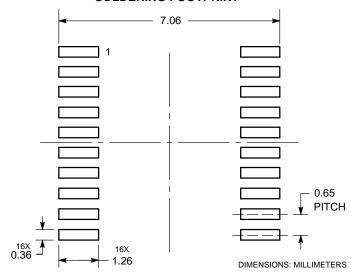
- 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE
- MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.060) PER SIDE.

  4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.

  5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION. ALLOWABLE (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
- CONDITION.
  6. TERMINAL NUMBERS ARE SHOWN FOR
- 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE –W–.

	MILLIN	IETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	6.40	6.60	0.252	0.260	
В	4.30	4.50	0.169	0.177	
С	-	1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65	BSC	0.026 BSC		
Н	0.27	0.37	0.011	0.015	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40	BSC	0.252 BSC		
M	0°	8°	0°	8°	

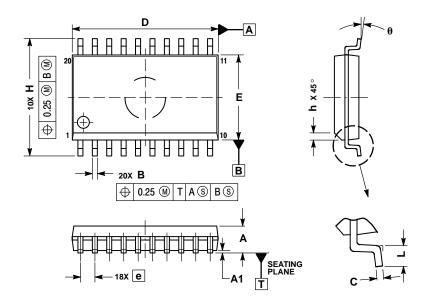
## **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

## PACKAGE DIMENSIONS

SOIC-20 CASE 751D-05 ISSUE G



#### NOTES:

- DIMENSIONS ARE IN MILLIMETERS.
- INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.
- 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSION.
- 4. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
- MAXIMUM MOLD PROTROSION 1.15 FEA 318
   DIMENSION B DOES NOT INCLUDE DAMBAR
   PROTRUSION. ALLOWABLE PROTRUSION
   SHALL BE 0.13 TOTAL IN EXCESS OF B
   DIMENSION AT MAXIMUM MATERIAL
   CONDITION.

	MILLIMETERS				
DIM	MIN	MAX			
Α	2.35	2.65			
A1	0.10	0.25			
В	0.35	0.49			
С	0.23	0.32			
D	12.65	12.95			
Е	7.40	7.60			
е	1.27	BSC			
Н	10.05	10.55			
h	0.25	0.75			
L	0.50	0.90			
θ	0 °	7 °			

ON Semiconductor and the unare registered trademarks of Semiconductor Components Industries, LLC (SCILLC) or its subsidiaries in the United States and/or other countries. SCILLC owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of SCILLC's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent–Marking.pdf. SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product products are not application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if suc

## **PUBLICATION ORDERING INFORMATION**

#### LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA

Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com

N. American Technical Support: 800–282–9855 Toll Free USA/Canada
Europe, Middle East and Africa Technical Support:

Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910

Japan Customer Focus Center Phone: 81–3–5817–1050 ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative